



Sheet 1 of 6

Form 1449*	Atty. Docket No.: 303.672US1	Serial No. 09/483,881
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: January 18, 2000	Group: Unknown

## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date <input checked="" type="checkbox"/> Appropriate
(h)	2,842,438	07/08/1958	Saarivirta, M.J., et al.	75	153	1700 08/02/56
	4,762,728	08/09/1988	Keyser, T., et al.	427	38	11/26/85
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✓	5,891,797	04/06/1999	Farrar, P.A.	438	619	10/20/97
	5,994,777	11/30/1999	Farrar, P.A.	257	758	08/26/98

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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation <input checked="" type="checkbox"/> Yes   No

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(h)	"Brooks Model 5964 High Performance Metal Seal Mass Flow Controller (Introduced in 1991)", <u>Brooks Instrument</u> , <a href="http://www.frc.com/brooks/semiconductor/productsli.html">http://www.frc.com/brooks/semiconductor/productsli.html</a> , 1 page, (1991)
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Sheet 2 of 6

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Group: Unknown

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
lm	4,847,111 /	07/11/1989	Chow, Y.C., et al.	427	38	06/30/88
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	5,231,056 /	07/27/1993	Sandhu, G.S.	437	200	01/15/92
	5,654,245 /	08/05/1997	Allen, G.L.	438	629	03/23/93
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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lm	Shacham-Diamond, Y., et al., "Copper electroless deposition technology for ultra-large-scale-integration (ULSI) metallization", <u>Microelectronic Engineering</u> , NL, Vol. 33, No. 1, XP004054497, 47-58, (1997)
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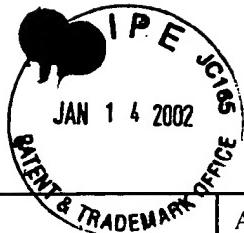
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	6,183,564	02/06/2001	Reynolds, G.J., et al.	118	719	11/12/98
	6,271,592	08/07/2001	Kim, E., et al.	257	751	08/06/99

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